

Top View

www.vishay.com

Vishay Siliconix

N-Channel 20 V (D-S) MOSFET

PowerPAK® 1212-8SH

Bottom View

PRODUCT SUMMARY	
V _{DS} (V)	20
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 10 \text{ V}$	0.0048
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 4.5 \text{ V}$	0.0063
Q _g typ. (nC)	16.7
I _D (A) ^a	35
Configuration	Single

FEATURES

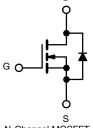
- TrenchFET® power MOSFET
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



FREE

APPLICATIONS

- DC/DC converter
 - Notebook
 - POL



N-Channe	MOSFET
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ORDERING INFORMATION	
Package	PowerPAK 1212-8
Lead (Pb)-free and halogen-free	SiSH410DN-T1-GE3

PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V_{DS}	20	\/	
Gate-source voltage		V_{GS}	± 20	V	
	T _C = 25 °C		35 ^a		
Continuous drain current (T _J = 150 °C)	T _C = 70 °C	1 .	35 ^a		
	T _A = 25 °C	l _D	22 ^{b, c}	A	
	T _A = 70 °C	1	17.8 ^{b, c}	A	
Pulsed drain current		I _{DM}	60		
Avalanche current	L = 0.1 mH	I _{AS}	35		
Avalanche energy		E _{AS}	61	mJ	
Continuous source-drain diode current	T _C = 25 °C	_	43	^	
Continuous source-drain diode current	T _A = 25 °C	l _S	3.2 b, c	Α	
	T _C = 25 °C		52		
Maximum power dissipation	T _C = 70 °C] р	33	w	
Maximum power dissipation	T _A = 25 °C	P _D	3.8 b, c	VV	
	T _A = 70 °C	1	2.4 ^{b, c}		
Operating junction and storage temperature	range	T _J , T _{stg}	-55 to +150	°C	
Soldering recommendations (peak temperature) d, e			260	-0	

THERMAL RESISTANCE RAT	NGS				
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient b, f	t ≤ 10 s	R_{thJA}	24	33	°C/W
Maximum junction-to-case (drain)	Steady state	R_{thJC}	1.9	2.4	\ \ \C/\v

Notes

- a. Package limited
- b. Surface mounted on 1" x 1" FR4 board
- See solder profile (www.vishay.com/doc?73257). The PowerPAK 1212-8SH is a leadless package within the PowerPAK 1212-8 package family. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components Maximum under steady state conditions is 81 °C/W

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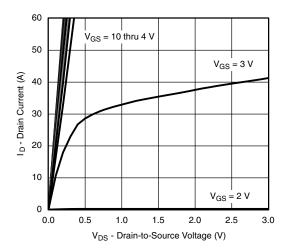
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	20	-	-	V
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$	I 050 A	-	19	-	m\//°C
V _{GS(th)} temperature coefficient	$\Delta V_{GS(th)}/T_J$	l _D = 250 μA	-	-5.3	-	mV/°C
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_{D} = 250 \ \mu A$	1.2	-	2.5	V
Gate-source leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
Zone sets veltere due in comment		V _{DS} = 20 V, V _{GS} = 0 V	-	-	1	
Zero gate voltage drain current	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V, T _J = 55 °C	-	-	5	μΑ
On-state drain current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	40	-	-	Α
Duit and an all the second	_	V _{GS} = 10 V, I _D = 20 A	-	0.0040	0.0048	_
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 19.4 A	-	0.0050	0.0063	Ω
Forward transconductance a	9 _{fs}	V _{DS} = 15 V, I _D = 20 A	-	70	-	S
Dynamic ^b						
Input capacitance	C _{iss}		-	1600	-	
Output capacitance	C _{oss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz	-	500	-	pF
Reverse transfer capacitance	C _{rss}			200	-	1
		V _{DS} = 10 V, V _{GS} = 10 V, I _D = 20 A	-	27	41	
Total gate charge	Q_g		-	16.7	25	
Gate-source charge	Q _{gs}	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 20 \text{ A}$	-	4.5	-	nC
Gate-drain charge	Q _{ad}		-	3.5	-	
Gate resistance	R _q	f = 1 MHz	-	1.3	2.6	Ω
Turn-on delay time	t _{d(on)}		-	25	40	
Rise time	tr	$V_{DD} = 10 \text{ V}, R_{I} = 1 \Omega$	-	15	25	
Turn-off delay time	t _{d(off)}	$I_D \cong 10 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$	-	30	45	
Fall time	t _f		-	15	25	1
Turn-on delay time	t _{d(on)}		-	12	20	ns
Rise time	t _r	$V_{DD} = 10 \text{ V}, R_{I} = 1 \Omega$	-	10	15	= = -
Turn-off delay time	t _{d(off)}	$I_D \cong 10 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	25	40	
Fall time	t _f		-	10	15	
Drain-Source Body Diode Characterist	•					
Continuous source-drain diode current	Is	T _C = 25 °C	-	-	43	_
Pulse diode forward current	I _{SM}	-	-	-	60	Α
Body diode voltage	V _{SD}	I _S = 10 A, V _{GS} = 0 V	-	0.8	1.2	V
Body diode reverse recovery time	t _{rr}		-	30	45	ns
Body diode reverse recovery charge	Q _{rr}	I _F = 10 A, di/dt = 100 A/μs,	_	21	35	nC
Reverse recovery fall time	t _a	$T_{\rm J} = 25 ^{\circ}{\rm C}$	_	17	-	
Reverse recovery rise time	t _b	-	_	13	_	ns

Notes

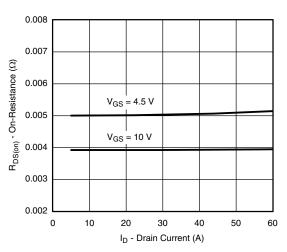
- a. Pulse test: pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

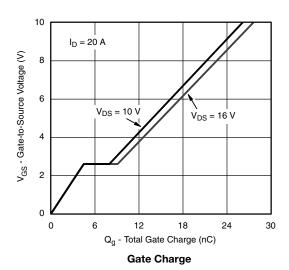


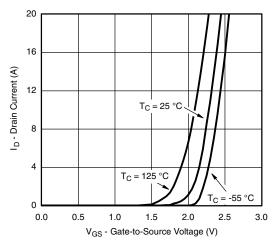


Output Characteristics

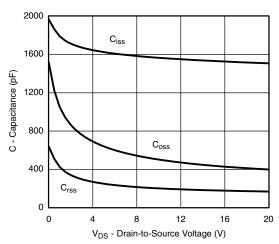


On-Resistance vs. Drain Current and Gate Voltage

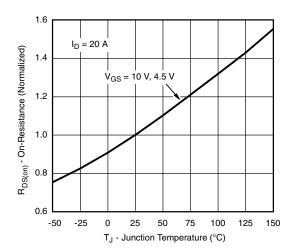




Transfer Characteristics

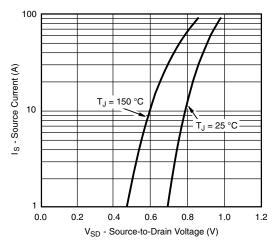


Capacitance

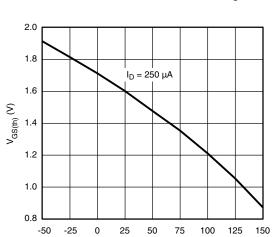


On-Resistance vs. Junction Temperature



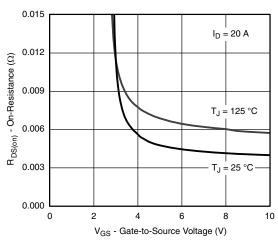


Source-Drain Diode Forward Voltage

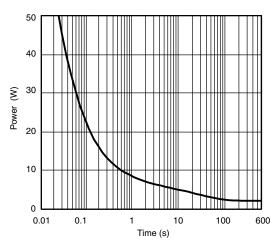


T_J - Temperature (°C)

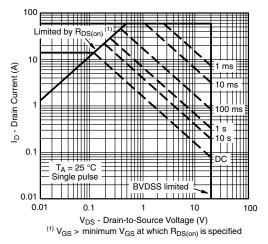
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage

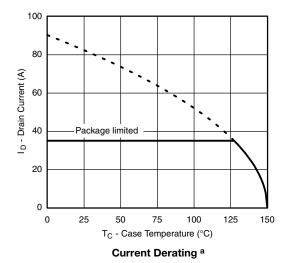


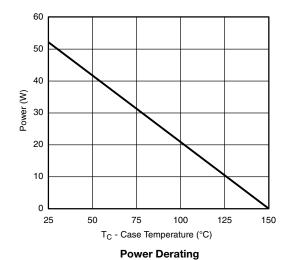
Single Pulse Power (Junction-to-Ambient)



Safe Operating Area, Junction-to-Ambient



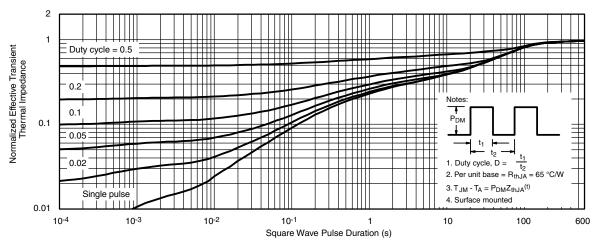




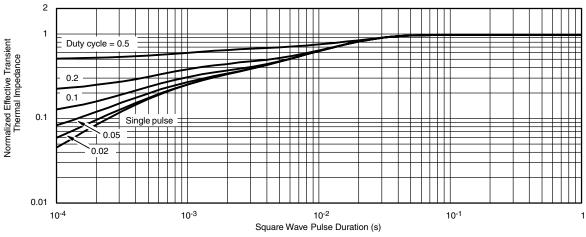
Note

a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit





Normalized Thermal Transient Impedance, Junction-to-Ambient



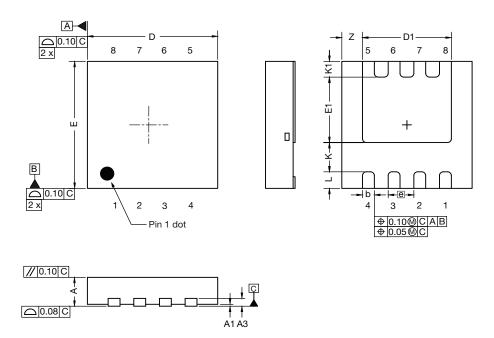
Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?79280.



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Case Outline for PowerPAK® 1212-SWLH and PowerPAK® 1212-8SH



DIM	MILLIMETERS			INCHES			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
Α	0.82	0.90	0.98	0.032	0.035	0.038	
A1	0.00	-	0.05	0.000	-	0.002	
A3		0.20 ref.		0.008 ref.			
b	0.25	0.30	0.35	0.010	0.012	0.014	
D	3.20	3.30	3.40	0.126	0.130	0.134	
D1	2.15	2.25	2.35	0.085	0.089	0.093	
E	3.20	3.30	3.40	0.126	0.130	0.134	
E1	1.60	1.70	1.80	0.063	0.067	0.071	
е	0.65 bsc.			0.026 bsc.			
K		0.76 ref.			0.030 ref.		
K1	0.41 ref.			0.016 ref.			
L	0.33	0.43	0.53	0.013	0.017	0.021	
Z	0.525 ref.			0.021 ref.			

DWG: 6062



RECOMMENDED MINIMUM PADS FOR PowerPAK® 1212-8 Single



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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